

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Leonard Forbes et al.

Title: DEAPROM AND TRANSISTOR WITH GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE

Docket No.: 303.355US4

Filed: June 18, 2001

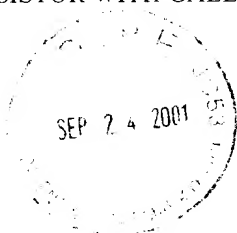
Examiner: Unknown

Serial No.: 09/883,795

Due Date: N/A

Group Art Unit: 2814

Commissioner for Patents
Washington, D.C. 20231



We are transmitting herewith the following attached items (as indicated with an "X"):

- ☒ A return postcard.
- ☒ Supplemental Preliminary Amendment (8 Pages).
- ☒ A check in the amount of \$590.00 to cover the fee for additional claims as calculated below.
- ☒ Clean Version of Pending Claims (8 pgs.).

If an additional fee is required due to changes to the claims, the fee has been calculated as follows:

CLAIMS AS AMENDED						
	(1) Claims Remaining After Amendment		(2) Highest Number Previously Paid For	(3) Present Extra	Rate	Fee
TOTAL CLAIMS	35	-	20	15	x 18 =	\$270.00
INDEPENDENT CLAIMS	7	-	3	4	x 80 =	\$320.00
[] MULTIPLE DEPENDENT CLAIMS PRESENTED						\$0.00
TOTAL						\$590.00

Please consider this a **PETITION FOR EXTENSION OF TIME** for sufficient number of months to enter these papers and please charge any additional required fees or credit overpayment to Deposit Account No. 19-0748

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
P.O. Box 2938, Minneapolis, MN 55402 (612-373-6900)

By:
Atty: Robert E. Mates
Reg. No. 35,271

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Commissioner for Patents, Washington, D.C. 20231, on this 18th day of September, 2001.

Name Amy McCarthy

Signature Amy McCarthy

Customer Number 21186

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
(GENERAL)

P.O. Box 2938, Minneapolis, MN 55402 (612-373-6900)

S/N 09/883,795

PATENT

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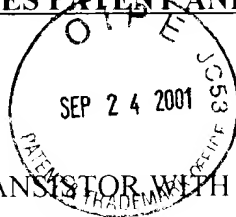
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#4/B
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Payto

SUPPLEMENTAL PRELIMINARY AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

Before taking up the above-identified application for examination, please enter the following amendments. Please substitute the claim set in the appendix entitled Clean Version of Pending Claims for the previously pending claim set.

IN THE CLAIMS

Please amend the following claims and add claims 30- 61:

24. (Amended) A method of forming a floating gate transistor[, the method] comprising:
forming a source region and a drain region[s] in a substrate;
forming a gate insulator [~~from the gate insulator material~~] comprising silicon dioxide (SiO₂) on a channel region in the substrate between the source region and the drain region; and
forming a floating gate [~~from~~] comprising a floating gate material selected from the group consisting [essentially] of gallium nitride (GaN) and gallium aluminum nitride (GaAlN), such that the floating gate is isolated from conductors and semiconductors.
25. (Amended) The method of claim 24[,] wherein forming [the] a floating gate [includes] further comprises forming the floating gate by depositing the floating gate material by metal organic chemical vapor deposition (MOCVD).
26. (Amended) The method of claim 24[,] wherein forming [the] a floating gate [includes] further comprises forming the floating gate material by plasma-enhanced molecular beam epitaxy (PEMBE).

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02 FC:103

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